

VDIC EEPROM

VDEE1M08XS40XX1C250 USER MANUAL

Version : A5

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VDIC-EEPROM

5.0V 128K × 8bit

1 Description

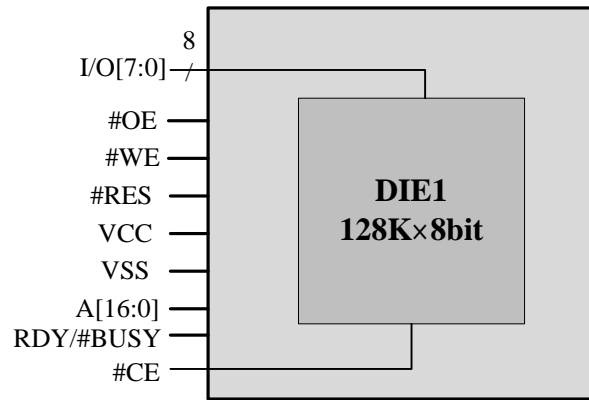
The VDEE1M08XS40XX1C250 is a 131.072 words of 8-bit. Electrically Erasable and Programmable CMOS ROM . It is organized with one bank of 1Mbit . This module operates at high speed, low power consumption and high reliability by employing advanced NMOS memory technology and CMOS process and circuitry technology. It is particularly well suited for use in high reliability, high performance and high density system applications.

The VDEE1M08XS40XX1C250 is packaged in a 40 pins SOP.

2 Features

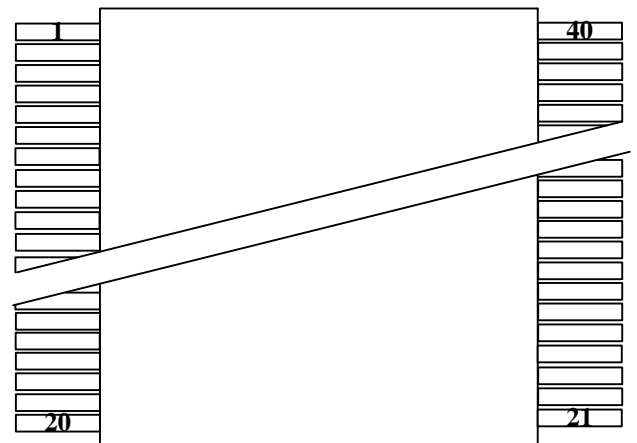
- Single 5.0V supply: 4.5 V to 5.5 V
- Access time: 150 ns (max)
- Power dissipation
 - Active: 20 mW/MHz, (typ)
 - Standby: 110 μ W (max)
- On-chip latches: address, data, #CE0, #OE, #WE
- Automatic byte write: 15 ms (max)
- Automatic page write (128 bytes): 15 ms (max)
- Data polling and RDY/#Busy
- Reliable CMOS with MNOS cell technology
- 10⁴erase/write cycles (in page mode)
- 10 years data retention
- Software data protection
- Write protection by #RES pin

3 Block Diagram



4 Pin Descriptions

| Pin Id | Pin # | | Pin Id |
|-----------|-------|----|--------|
| VSS | 1 | 40 | NC |
| NC | 2 | 39 | NC |
| A11 | 3 | 38 | #OE |
| A9 | 4 | 37 | A10 |
| A8 | 5 | 36 | #CE0 |
| A13 | 6 | 35 | I/O7 |
| #WE | 7 | 34 | I/O6 |
| #RES | 8 | 33 | I/O5 |
| A15 | 9 | 32 | I/O4 |
| VCC | 10 | 31 | I/O3 |
| RDY/#BUSY | 11 | 30 | VSS |
| A16 | 12 | 29 | I/O2 |
| A14 | 13 | 28 | I/O1 |
| A12 | 14 | 27 | I/O0 |
| A7 | 15 | 26 | A0 |
| A6 | 16 | 25 | A1 |
| A5 | 17 | 24 | A2 |
| A4 | 18 | 23 | A3 |
| NC | 19 | 22 | NC |
| NC | 20 | 21 | NC |



| Name | Function |
|------------|--|
| A0~A16 | Address Input.. |
| I/O0- I/O7 | Data Input/Output Ports. 8 bit-directional ports are used to read data from or |

| | |
|-----------|--|
| | write data into the EEPROM. |
| #CE0 | Die Enable Input .When #CE0 is Low, the command input cycle becomes valid. When #CE0 is High, input are ignored. |
| RDY/#BUSY | Ready busy. |
| #RES | Reset input. |
| #OE | Output enable. |
| #WE | Write Enable Input. Enables write operation. |
| VCC | Power supply |
| VSS | Ground |
| NC | No connection This pin is recommended to be left No Connection on the device. |

5 Electrical Specifications

5.1 Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|------------------|--------------|------|
| Supply voltage relative toV _{SS} | V _{CC} | -0.6 to +7.0 | V |
| Input voltage relative toV _{SS} | V _{IN} | -0.5to +7.0 | V |
| Operating temperature range | T _{OPR} | -55 to +125 | °C |
| Storage temperature range | T _{STG} | -65 to +150 | °C |
| Power Dissipation | P _D | 2 | W |

5.2 Recommended DC Operating Conditions

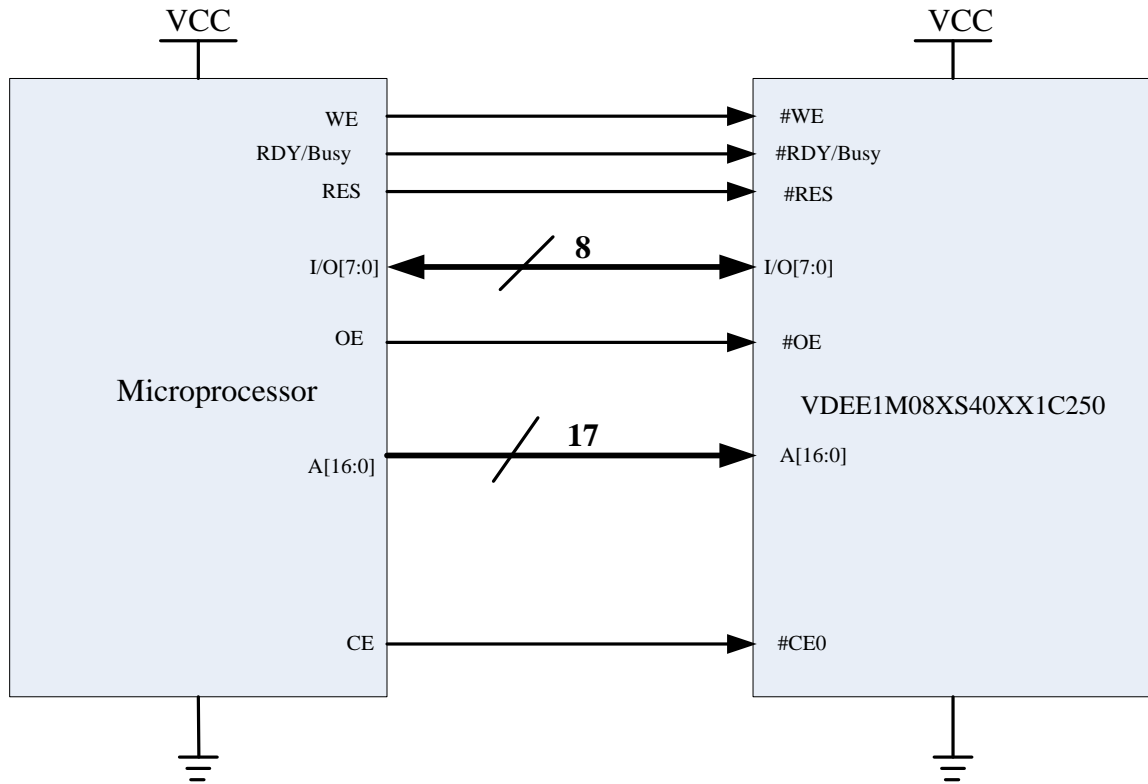
| Parameter | Symbol | Min | Typ | Max | Unit |
|----------------|-----------------|----------------------|-----|----------------------|------|
| Supply voltage | V _{CC} | 4.5 | 5.0 | 5.5 | V |
| | V _{SS} | 0 | 0 | 0 | V |
| Input voltage | V _{IL} | -0.3 | - | 0.8 | V |
| | V _{IH} | 2.2 | - | V _{CC} +0.3 | V |
| | V _H | V _{CC} -0.5 | - | V _{CC} +1.0 | V |

5.3 DC Characteristics (VCC = 4.5 V to 5.5 V)

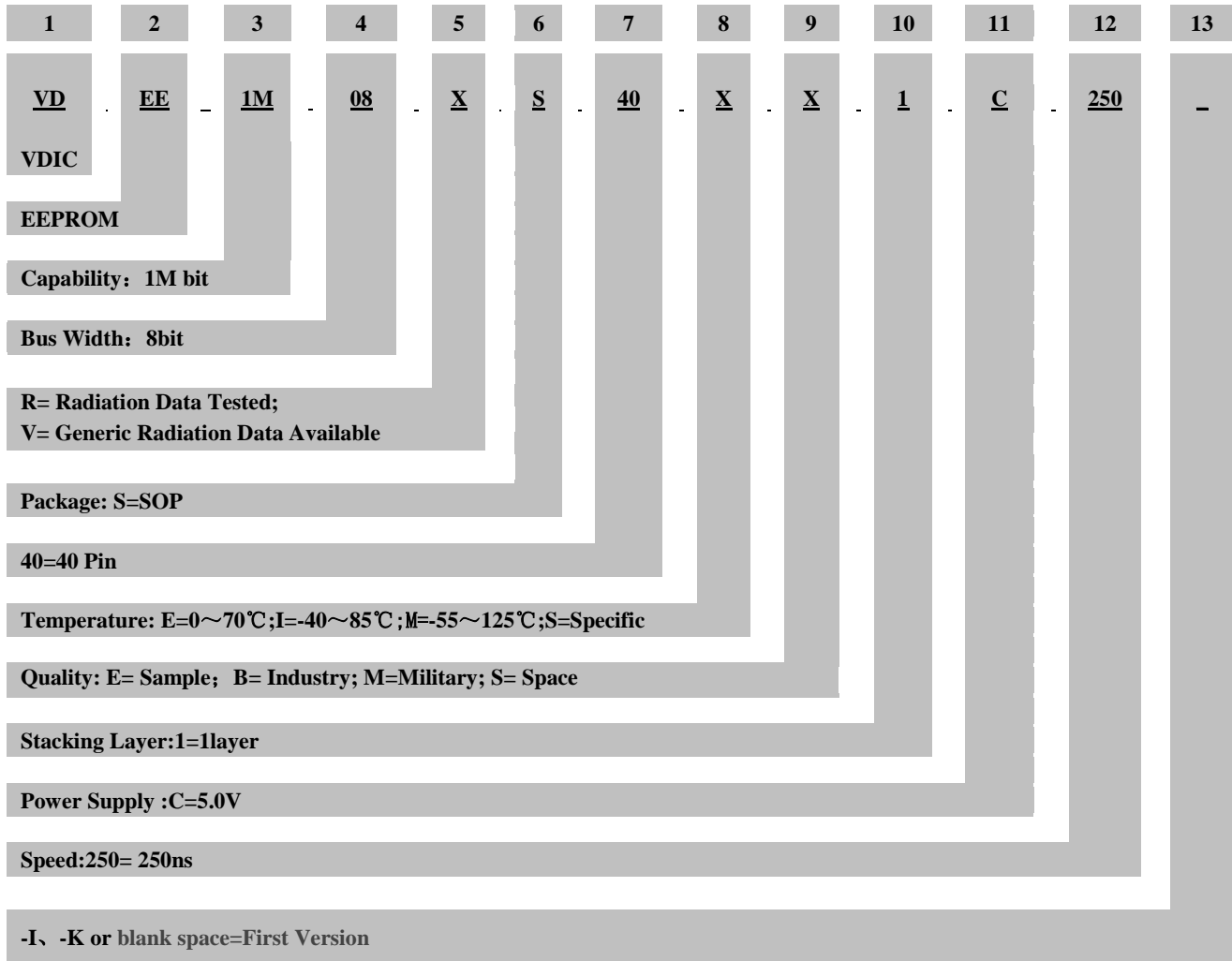
| Parameter | Symbol | Test conditions | min. | max. | Unit |
|--------------------------|--------|---|------|------|------|
| Output voltage low level | VOL | V _{CC} =4.5V , I _{OL} = 2.1mA | — | 0.4 | V |

| Parameter | Symbol | Test conditions | min. | max. | Unit |
|---------------------------|--------|--|------|------|------|
| Output voltage high level | VOH | V _{CC} =4.5V , I _{OH} = -400uA | 2.4 | — | V |

6 Typical Application



7 Ordering Information



| Part Number | Capacity (bit) | Bus Width (bit) | Radiation | | | Packaging | Temperature (°C) |
|---------------------|----------------|-----------------|------------------|------------------|------------------|-----------|--------------------|
| | | | TID ¹ | SEL ² | SEU ³ | | |
| VDEE1M08VS40EE1C250 | 1M | 8 | - | - | - | SOP40 | 0 ~ + 70 |
| VDEE1M08VS40IB1C250 | 1M | 8 | - | - | - | SOP40 | -40 ~ + 85 |
| VDEE1M08VS40MB1C250 | 1M | 8 | - | - | - | SOP40 | -55 ~ + 125 |
| VDEE1M08VS40MM1C250 | 1M | 8 | - | - | - | SOP40 | -55 ~ + 125 |

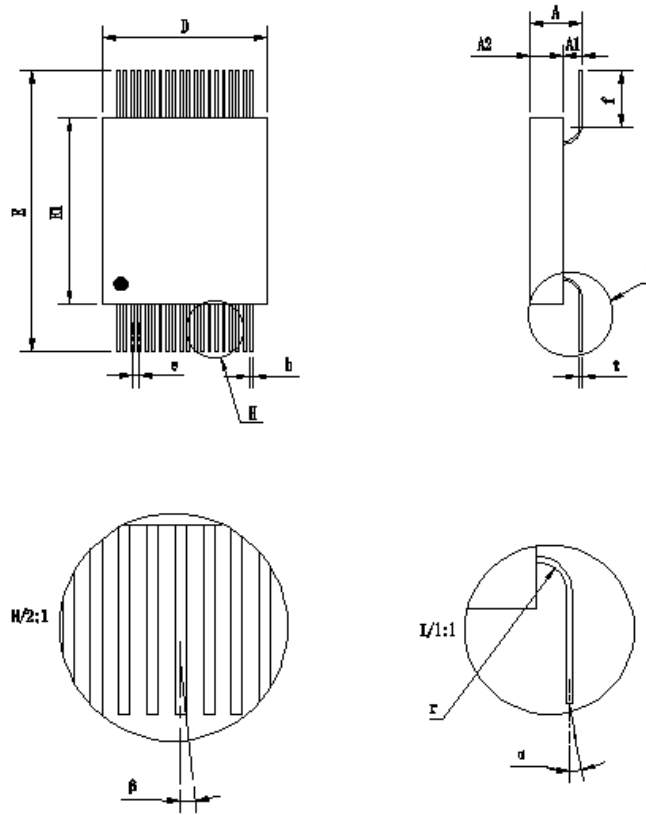
¹ TID: Total Dose (Krad(Si))

² SEL: LET Threshold (Mev.cm²/mg)

³ SEU:SEU Threshold (Mev.cm²/mg)

| | | | | | | | |
|---------------------|----|---|----|------|----|-------|-------------|
| VDEE1M08RS40MS1C250 | 1M | 8 | 30 | 99.8 | 25 | SOP40 | -55 ~ + 125 |
|---------------------|----|---|----|------|----|-------|-------------|

8 Package Dimensions



| | Min | Max |
|---------------------|----------------|-------|
| A | 3.80 | 4.30 |
| A2 | 2.60 | 3.00 |
| D | 11.50 | 11.90 |
| E | 19.80 | 20.20 |
| E1 | 13.00 | 13.40 |
| f | 3.98 | |
| b | 0.25 | |
| e | 0.5 | |
| r | 1.0 | |
| t | 0.2 | |
| α | $\leq 3^\circ$ | |
| β | $\leq 3^\circ$ | |
| NOTE : 1.U int : mm | | |
| 2. A1= A - A2 | | |

9 REVISION HISTORY

| Revision | Date | Description of Change |
|----------|-------------|---|
| A0 | Nov 3,2015 | First Created |
| A1 | Mar 14,2016 | Modified the PIN DESCRIPTIONS |
| A2 | Aug 23,2016 | Modified the ORDERING INFORMATION |
| A3 | Jan 9,2017 | Modified the PACKAGE DIMENSIONS |
| A4 | Oct.25,2017 | Changed company's name to Zhuhai Orbita Aerospace Science & Technology Co., Ltd |
| A5 | Mar 16,2018 | Add or reduce chapters |